

CLAIMS

1. A substrate dividing method comprising the steps of:

irradiating a substrate with laser light while positioning a
5 light-converging point within the substrate, so as to form a
modified region due to multiphoton absorption within the
substrate, and causing the modified region to form a starting
point region for cutting along a line along which the substrate
should be cut in the substrate inside by a predetermined distance
10 from a laser light incident face of the substrate; and

grinding the substrate after the step of forming the starting
point region for cutting such that the substrate attains a
predetermined thickness.

2. A substrate dividing method according to claim 1,
15 wherein the substrate is a semiconductor substrate.

3. A substrate dividing method according to claim 2,
wherein the modified region is a molten processed region.

4. A substrate dividing method according to claim 1,
wherein the substrate is an insulating substrate.

20 5. A substrate dividing method according to one of
claims 1 to 4, wherein a front face of the substrate is formed with
a functional device; and

wherein a rear face of the substrate is ground in the step of
grinding the substrate.

25 6. A substrate dividing method according to claim 5,
wherein the step of grinding the substrate includes a step of

subjecting the rear face of the substrate to chemical etching.